30V P-Channel Enhancement Mode MOSFET

Description

The NP3401 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

V_{DS} =-30V I_D =-4.2A

$R_{DS(ON)}$(Typ.)=53mÝ @V_{GS}=-4.5V

$R_{DS(ON)}$(Typ.)=73mÝ @V_{GS}=-2.5V

High power and current handing capability

Lead free product is acquired

Surface mount package

Application

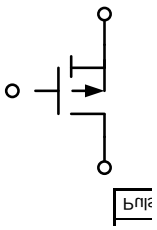
PWM applications

Load switch

Package

SOT-23

Schematic diagram



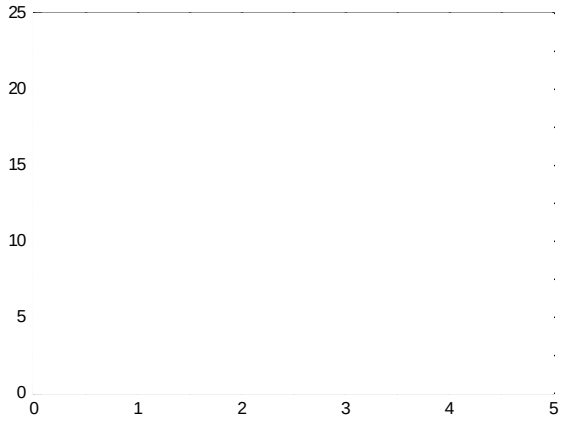
Maximum power dissipation	T_C=25°C	P_D	1.7	W
	T_C=70°C		1.1	
	T_A=25°C		1[b,c]	
	T_A=70°C		0.6[b,c]	
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55—150	

Thermal Characteristics

Parameter	Symbol	Typical	Maximum	Unit

DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode forward voltage	V_{SD}	V_{GS}=0V,Is=-4A	-	-0.81	-1.2	V

Typical Performance Characteristics



Package Information

SOT-23

